

Notice of References CitedApplication/Control No.
09/588,008Applicant(s)/Patent Under
Reexamination:
YANG ET AL.Examiner
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2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6489199	12-2002	Li et al.	438/253
	B	US-			
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	F	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Yamagishi et al., Stacked Capacitor DRAM process using photo-CVD Ta ₂ O ₅ , Electron Devices, IEEE Transaction on, Volume 35 Issue: 12, Dec 1988, p. 2439.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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